

GD54/74HC244, GD54/74HCT244

OCTAL NONINVERTING 3-STATE BUFFERS

General Description

These devices are identical in pinout to the 54/74LS244. They contain eight noninverting buffers with two active-low enables. Each enable independently controls 4 buffers. These octal noninverting buffers/line drivers/line receivers are designed to be used with 3-state memory address drivers. Clock drivers, and other bus-oriented systems. Refer to the other devices for similar functionality:

HC/HCT 240 Inverting, active-low enables

HC/HCT 241 Noninverting, active-low

& active-high enables

These devices are characterized for operation over wide temperature ranges to meet industry and military specifications.

Features

- Low Power consumption characteristic of CMOS devices
 - Output drive capability 15 LS TTL Loads Min
 - Operating speed superior to LS TTL
 - Wide operating voltage range for HC 2 to 6 volts
for HCT 4.5 to 5.5 volts
 - Low input current 1 μ A Max
 - Low quiescent current. 80 μ A Max. (74HC)
 - High noise immunity characteristic of CMOS
 - Diode protection on all inputs

Function Table

INPUTS		OUTPUT
$n\overline{OE}$	nA_n	nY_n
L	L	L
L	H	H
H	X	Z

H = HIGH voltage level

L = LOW voltage level

X = don't care

Z = high impedance OFF-state

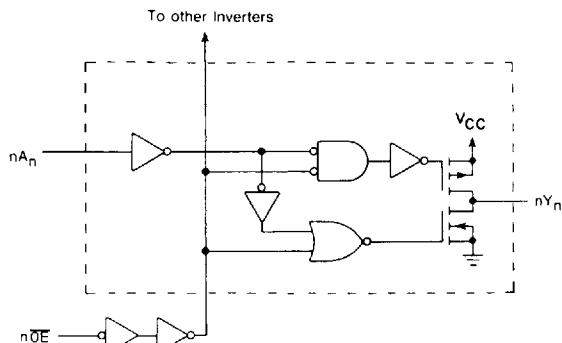


Fig. 1 Logic diagram (one gate)

Absolute Maximum Ratings

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{CC}	DC Supply voltage		-0.5	+7	V
I_{IK}, I_{OK}	DC input or output diode current	for $V_i < -0.5$ or $V_i > V_{CC} + 0.5V$	20	mA	
I_O	DC output source or sink current	for $-0.5V < V_O < V_{CC} + 0.5V$	35	mA	
I_{CC}	DC V_{CC} or GND current		70	mA	
T_{STG}	Storage temperature range		-65	150	°C
P_D	Power dissipation per package	above $+70^\circ\text{C}$ derate linearly with 8mW/K		500	mW
T_L	Lead temperature	At distance 1.16 ± 1.32 in from case for 60 sec(CERAMIC) 10 sec(PLASTIC)		300 260	°C

Recommended Operating Conditions

CHARACTERISTIC	LIMITS		UNITS
	MIN	MAX	
Supply-Voltage Range V_{CC} GD54/74HC Types GD54/74HCT Types	2 4.5	6 5.5	V
DC Input or Output Voltage V_i, V_O	0	V_{CC}	V
Operating Temperature T_A GD74 Types GD54 Types	-40 -55	+85 +125	°C
Input Rise and Fall times t_r, t_f GD54/74HC Types at 2V at 4.5V at 6V , GD54/74HCT Types at 4.5V		1000 500 400 500	ns

Logic Diagram

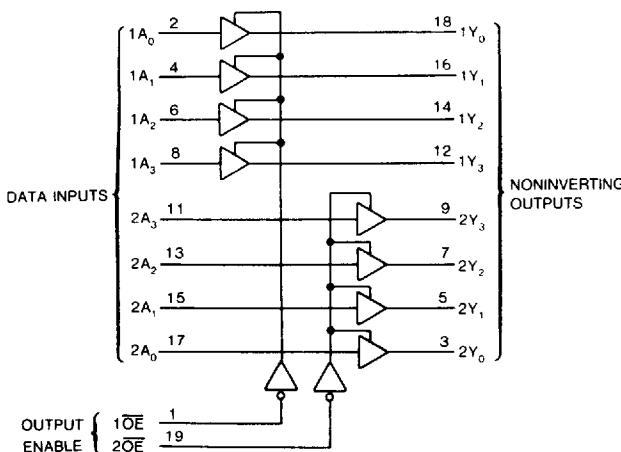


Fig. 2 Logic diagram

DC Electrical Characteristics for HC

SYMBOL	PARAMETER	TEST CONDITION	V _{CC} (V)	T _A =25°C			GD74HC244		GD54HC244		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V _{IH}	HIGH level input Voltage		2 0 4 5 6 0	1 5 3 15 4 2			1 5 3 15 4 2		1 5 3 15 4 2		V
V _{IL}	LOW level input voltage		2 0 4 5 6 0			0 3 0 9 1 2		0 3 0 9 1 2		0 3 0 9 1 2	V
V _{OH}	HIGH level output voltage	V _{IN} =V _{IH}	I _{OH} =-20μA	2 0 4 5 6 0	1 9 4 4 5 9	2 0 4 5 6 0		1 9 4 4 5 9		1 9 4 4 5 9	V
			I _{OH} =-6mA	4 5 6 0	3 98 5 48	4 3 5 2		3 84 5 34		3 7 5 2	
		or V _{IL}	I _{OH} =-7.8mA								
			I _{OL} =20μA	2 0 4 5 6 0		0 1 0 1 0 1		0 1 0 1 0 1		0 1 0 1 0 1	V
V _{OL}	LOW level output voltage	V _{IN} =V _{IH}	I _{OL} =6mA	4 5 6 0		0 17 0 15	0 26 0 26		0 33 0 33		V
			I _{OL} =7.8mA								
		or V _{IL}									
I _{IN}	Input leakage Current	V _{IN} =V _{CC} or GND	6 0			0 1		1 0		1 0	μA
I _{OZ}	Three State leakage current	V _{IN} =V _{IH} or V _{IL}	V _O =V _{CC} or GND	6 0		0 01 0 5		5 0		10 0	μA
I _{CC}	Quiescent Supply Current	V _{IN} =V _{CC} or GND I _{out} =0μA	6 0			8		80		160	μA

DC Electrical Characteristics for HCT

SYMBOL	PARAMETER	TEST CONDITION	V _{CC} (V)	T _A =25°C			GD74HCT244		GD54HCT244		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V _{IH}	HIGH level input Voltage		4 5 to 5 0	2 0			2 0		2 0		V
V _{IL}	LOW level input voltage		4 5 to 5 5			0 8		0 8		0 8	V
V _{OH}	HIGH level output voltage	V _{IN} =V _{IH}	I _{OH} =-20μA	4 5	4 4	4 5		4 4		4 4	V
			I _{OH} =-6mA	4 5	3 98	4 3		3 84		3 7	
		or V _{IL}	I _{OH} =-7.8mA								
			I _{OL} =20μA	4 5		0 1		0 1		0 1	V
V _{OL}	LOW level output voltage	V _{IN} =V _{IH}	I _{OL} =6mA	4 5		0 17	0 26		0 33		V
			I _{OL} =7.8mA								
		or V _{IL}									
I _{IN}	Input leakage Current	V _{IN} =V _{CC} or GND	5 5			0 1		1 0		1 0	μA
I _{OZ}	Three State leakage current	V _{IN} =V _{IH} or V _{IL}	V _O =V _{CC} or GND	5 5		0 01 0 5		5 0		10 0	μA
I _{CC}	Quiescent Supply Current	V _{IN} =V _{CC} or GND I _{out} =0μA	5 5			8		80		160	μA

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AC Characteristics for HC: $t_r=t_f=6\text{ ns}$ $C_L=50\text{ pF}$

SYMBOL	PARAMETER	V_{CC} (V)	$T_A=25^\circ\text{C}$			GD74HC244		GD54HC244		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{PLH} / t_{PHL}	Propagation Delay Time nA_n to nY_n	2.0		30	100			120		ns
		4.5		9	18			24		
		6.0		8	16			20		
t_{PZH} / t_{PZL}	3-state Output Enable Time $n\overline{OE}$ to nY_n	2.0		35	140			180		ns
		4.5		10	28			36		
		6.0		9	26			32		
t_{PLZ} / t_{PHZ}	3-state Output Disable Time $n\overline{OE}$ to nY_n	2.0		35	140			180		ns
		4.5		10	28			36		
		6.0		9	26			32		
t_{TLH} / t_{THL}	Output Transition Time	2.0		15	60			75		ns
		4.5		6	12			15		
		6.0		5	10			13		

AC Characteristics for HCT: $t_r=t_f=6\text{ ns}$ $C_L=50\text{ pF}$

SYMBOL	PARAMETER	V_{CC} (V)	$T_A=25^\circ\text{C}$			GD74HCT244		GD54HCT244		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{max}	Propagation Delay Time nA_n to nY_n	4.5		12	22			26		30 ns
t_{PLH} / t_{PHL}	Propagation Delay Time $n\overline{OE}$ to nY_n	4.5		18	30			38		45 ns
t_{PLH} / t_{PHL}	Propagation Delay Time $n\overline{OE}$ to nY_n	4.5		15	25			32		38 ns
t_{TLH} / t_{THL}	Output Transition Time	4.5		7	12			15		18 ns

AC Waveforms

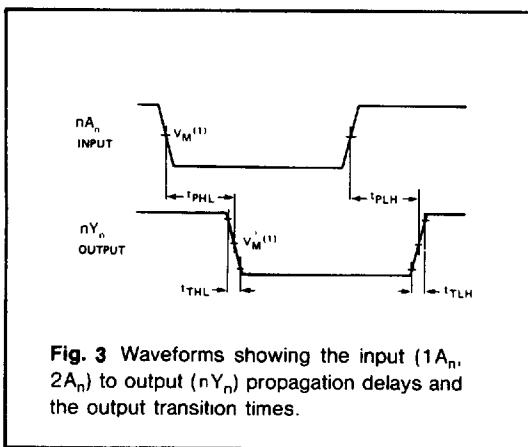


Fig. 3 Waveforms showing the input (nA_n , $2A_n$) to output (nY_n) propagation delays and the output transition times.

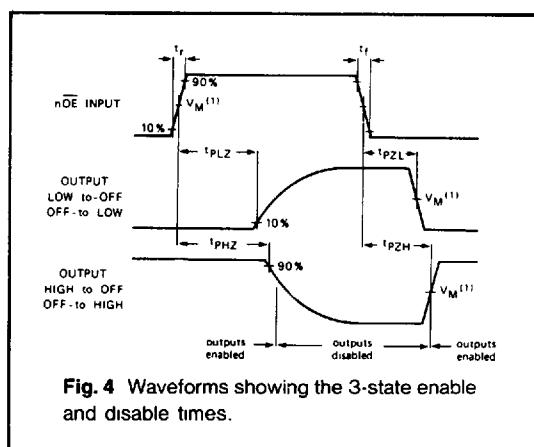


Fig. 4 Waveforms showing the 3-state enable and disable times.